

# Comparison of proton damage in thin FZ, MCz and epitaxial silicon detectors

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We present results on 24 GeV/c proton irradiated thin n-type FZ (50  $\mu\text{m}$ , 100  $\mu\text{m}$ ), MCz (100  $\mu\text{m}$ ), epitaxial (72, 100, 150  $\mu\text{m}$ , standard and oxygenated) pad detectors. Annealing experiments at 80°C have been performed. The extracted macroscopic damage parameters and charge collection measurements with alpha particles will be presented.

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